REMARKS

Applicants present for prosecution in this application claims based on allowed parent application claims 6-9, 11, 14, 15, 18, 19, 21 and 23 that were canceled by the Amendment Under 37 CFR 1.312 filed January 2, 2002. The claim numbering starting at claim 16 is based on the fact that the claims as filed in the parent application should have been claims 1-15 as revised in the international stage and not original claims 1-11 as filed with the international application. The revised claims replaced the original claims during the parent prosecution, as they should have been deemed the original claims as filed of the parent application (and thus of this divisional application as well).

Applicants are in the process of preparing translations of prior art documents that the Examiner should consider in connection with the claims as provided above. Therefore, applicants respectfully request that this application not be examined until applicants can submit these translations.

Early action allowing claims 16-25 is solicited.

In the event that the transmittal letter is separated from this document and the Patent and Trademark Office determines that an extension and/or other relief is required, applicant petitions for any required relief including extensions of time and authorizes the Commissioner to charge the cost of such petitions and/or other fees due in connection with the filing of this document to **Deposit Account No. 03-1952**, Ref. 204552016410.

Respectfully submitted,

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Barry E. Bretschneider
Registration No. 28,055

Morrison & Foerster LLP
2000 Pennsylvania Avenue, N.W.
Washington, D.C. 20006-1888
Telephone: (703) 760-7710
Facsimile: (202) 263-8396

REVISED CLAIMS

(For US)

1. A gallium nitride semiconductor light emitting device, comprising a semiconductor substrate, an active layer having a quantum well structure and made of nitride semiconductor containing at least indium and gallium, and a first cladding layer and a second cladding layer for sandwiching the active layer therebetween, wherein

the active layer consists of two quantum well layers and one barrier layer interposed between the quantum well layers.

2. The gallium nitride semiconductor light emitting device according to Claim 1, wherein the active layer is configured so as to allow electrons and holes to be uniformly distributed in each of the quantum well layers.

3. The gallium nitride semiconductor light emitting device according to Claim 1, wherein the gallium nitride semiconductor light emitting device is a semiconductor laser device and the active layer forms an oscillating section of the semiconductor laser device.

4. The gallium nitride semiconductor light emitting device according to Claim 3, wherein the semiconductor laser device is a self-oscillating semiconductor laser device.

5. The gallium nitride semiconductor light emitting device according to Claim 1, wherein the barrier layer has a layer thickness of 10 nm or less.

6. A gallium nitride semiconductor light emitting device, comprising a semiconductor substrate, an active layer having a quantum well structure and made of nitride semiconductor containing at least indium and gallium, and a first cladding layer and a second cladding layer for sandwiching the active layer therebetween, wherein

the active layer comprises two to four quantum well layers and one to three barrier layers each interposed between the quantum well layers, and the one or each barrier layer has a layer thickness of 4 nm or less.

7. The gallium nitride semiconductor light emitting device according to Claim 6, wherein the active layer is configured so as to allow electrons and holes to be uniformly distributed in each of the quantum well layers.

8. The gallium nitride semiconductor light emitting device according to Claim 6, wherein the gallium nitride semiconductor light emitting device is a semiconductor laser device and the active layer forms an oscillating section of the semiconductor laser device.

9. The gallium nitride semiconductor light emitting device according to Claim 8, wherein the semiconductor laser device is a self-oscillating semiconductor laser device.

10. The gallium nitride semiconductor light emitting device according to Claim 1, wherein each quantum well layer has a layer thickness of 10 nm or less.

11. The gallium nitride semiconductor light emitting device according to Claim 6, wherein each quantum well layer has a layer thickness of 10 nm or less.

12. A semiconductor laser light source device, comprising the semiconductor laser device as defined in Claim 3, and a driving circuit for injecting an electric current into the semiconductor laser device.

13. The semiconductor laser light source device according to Claim 12, wherein the electric current is a

modulated current and a modulation frequency of the current is 300 MHz or more.

14. A semiconductor laser light source device, comprising the semiconductor laser device as defined in Claim 8, and a driving circuit for injecting an electric current into the semiconductor laser device.

15. The semiconductor laser light source device according to Claim 14, wherein the electric current is a modulated current and a modulation frequency of the current is 300 MHz or more.